

Fig. 3A is a schematic diagram to show directions of the fast axis at birefringence measuring points P_{31} , P_{32} , P_{33} , P_{34} and P_{35} located at respective distances r_1 , r_2 , r_3 , r_4 , and r_5 from the center O on the effective section of another optical member L_3 , similar to Fig 1A. In this case, the directions of the fast axis, W_{31} , W_{32} , W_{33} , W_{34} , and W_{35} , at the measuring points P_{11} to P_{14} are such that those at the measuring points P_{31} to P_{33} are parallel to the direction of the straight line Q_3 , i.e., to the radial direction, but those at the measuring points P_{33} , P_{34} are perpendicular to the radial direction. Therefore, the distribution in the radial direction of the signed birefringence values A_{31} to A_{35} at the measuring points P_{31} to P_{35} is depicted, for example, as a profile of Fig. 3B.

Page 54, lines 23-26 and Page 55, lines 1-14, delete current paragraph and insert therefor:

The wafer W is mounted on a leveling stage (not illustrated) and this leveling stage is set on a Z-stage 301 which can be finely moved in the optical-axis direction (Z-direction) of the projection optical

system by a driving motor 330. The Z-stage 301 is mounted on an XY stage 315 which can be moved in the two-dimensional directions (XY directions) in the step-and-repeat method by the driving motor 320. The reticle R is mounted on a reticle stage 306 which is two-dimensionally movable in the horizontal plane. The exposure light from the exposure light source 303 uniformly illuminates the pattern formed in the reticle R through the illumination optical system 302 and the pattern image of the reticle R is printed into a shot area of the wafer W by the projection optical system 304. This exposure light can be one of the wavelength selected from 248 nm (KrF excimer laser), 193 nm (ArF excimer laser), 157 nm (F₂ laser), and so on.

Page 58, lines 13-26 and Page 59, lines 1-13, delete current paragraph and insert

therefor:

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The exposure light source 303 (not illustrated) emits approximately collimated light having the wavelength of 248 nm (KrF excimer laser), 193 nm (ArF excimer laser), 157 nm (F₂ laser), or the like, and the cross-sectional shape of the collimated light at this time is rectangular. The collimated light from this exposure light source 303 is incident to a beam shaping optical system 20 as a beam shaping portion for shaping the beam into a predetermined sectional shape. This beam shaping optical system 20 is comprised of two cylindrical lenses (20A, 20B) each having a refractive power in the Y-direction; the source-side cylindrical lens 20A has a negative refractive power to diverge the X-directional beam, and the cylindrical lens 20B on the illuminated surface side has a positive refractive power to condense the diverging beam from the source-side cylindrical lens 20A into parallel light. Accordingly, after the collimated light from the exposure light source 303 passes through the beam shaping optical system 20, the Y-directional beam width is expanded, so that the cross section of the beam is shaped into a rectangular shape having a predetermined size. The beam shaping optical system 20 may also be comprised of a combination of cylindrical lenses of positive refractive power, an anamorphic prism, or the like.

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